

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2	("field oxide" near "active area") and field and epitaxial and substrate and gate and transistor and voltage and photodiode and (dop\$4 near region) and spacer and insulat\$4 and block and mask and float\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 11:12
S2	0	("field oxide" near active) and field and epitaxial and substrate and gate and transistor and voltage and photodiode and (dop\$4 near region) and spacer and insulat\$4 and block and mask and float\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:39
S3	0	(oxide near active) and field and epitaxial and substrate and gate and transistor and voltage and photodiode and (dop\$4 near region) and spacer and insulat\$4 and block and mask and float\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 11:39
S4	53	oxide and active and field and epitaxial and substrate and gate and transistor and voltage and photodiode and (dop\$4 near region) and spacer and insulat\$4 and block and mask and float\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:27
S5	0	"CMOS image sensor" and "spacer insulation layer" and nitride and oxide and angstrom	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:29
S6	51	"CMOS image sensor" and spacer and nitride and oxide and angstrom	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:29
S7	157	"CMOS image sensor" and spacer and nitride and oxide and (angstrom near nitride or oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:30
S8	374	"CMOS image sensor" and space and (angstrom near nitride or oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:30

S9	56	"CMOS image sensor" and (spacer near insulat\$4) and (angstrom near nitride or oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:31
S10	85	"CMOS image sensor" and (spacer near4 insulat\$4) and (angstrom near4 nitride or oxide)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/22 13:30
S11	219	oxide and active and epitaxial and (substrate or wafer or semiconductor) and gate and transistor and photodiode and voltage and dop\$4 and insulat\$4 and spacer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 11:17
S12	198	oxide and active and epitaxial and (substrate or wafer or semiconductor) and gate and transistor and photodiode and voltage and dop\$4 and insulat\$4 and spacer and CMOS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 11:18
S13	186	oxide and active and epitaxial and (substrate or wafer or semiconductor) and gate and transistor and photodiode and voltage and dop\$4 and insulat\$4 and spacer and CMOS and nitride	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 11:18
S14	110	oxide and active and epitaxial and (substrate or wafer or semiconductor) and gate and transistor and photodiode and voltage and dop\$4 and insulat\$4 and spacer and CMOS and nitride and thickness and angstrom	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 11:18
S15	110	oxide and active and epitaxial and (substrate or wafer or semiconductor) and gate and transistor and photodiode and voltage and dop\$4 and insulat\$4 and spacer and CMOS and nitride and thickness and angstrom and n-type and p-type	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 11:19

S16	108	oxide and active and epitaxial and (substrate or wafer or semiconductor) and gate and transistor and photodiode and voltage and dop\$4 and insulat\$4 and spacer and CMOS and nitride and thickness and angstrom and n-type and p-type and implant\$4 and mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 11:19
S17	35	oxide and active and epitaxial and (substrate or wafer or semiconductor) and gate and transistor and photodiode and voltage and dop\$4 and insulat\$4 and spacer and CMOS and nitride and thickness and angstrom and n-type and p-type and implant\$4 and mask and photoresist	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 11:20
S18	23	oxide and active and epitaxial and (substrate or wafer or semiconductor) and gate and transistor and photodiode and voltage and dop\$4 and insulat\$4 and spacer and CMOS and nitride and thickness and angstrom and n-type and p-type and implant\$4 and mask and photoresist and float\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/07/14 11:20